

**COMMON SOURCE DUAL N-CHANNEL  
ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

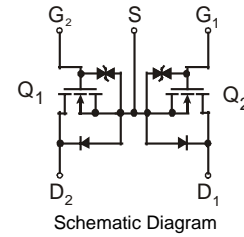
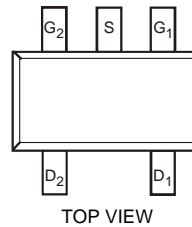
NEW PRODUCT

**Features**

- Common Source Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.2V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Small Surface Mount Package
- ESD Protected Gate
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q 101 Standards for High Reliability**



SOT-353



**Mechanical Data**

- Case: SOT-353
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

**Maximum Ratings**  $Q_1, Q_2$  @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic         | Symbol    | Value    | Unit |
|------------------------|-----------|----------|------|
| Drain Source Voltage   | $V_{DSS}$ | 30       | V    |
| Gate-Source Voltage    | $V_{GSS}$ | $\pm 10$ | V    |
| Drain Current (Note 1) | $I_D$     | 400      | mA   |

**Thermal Characteristics**  $Q_1, Q_2$  @ $T_A = 25^\circ\text{C}$  unless otherwise specified

|  |                 |             |                    |
|--|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 1)                 | $P_D$           | 280         | mW                 |
| Thermal Resistance, Junction to Ambient (Note 1) | $R_{\theta JA}$ | 446         | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range          | $T_j, T_{STG}$  | -55 to +150 | $^\circ\text{C}$   |

**Electrical Characteristics**  $Q_1, Q_2$  @ $T_A = 25^\circ\text{C}$  unless otherwise specified

| Characteristic   | Symbol        | Min       | Typ | Max                 | Unit          | Test Condition  |
|--|---------------|-----------|-----|---------------------|---------------|---|
| <b>OFF CHARACTERISTICS (Note 4)</b>                        |               |           |     |                     |               |   |
| Drain-Source Breakdown Voltage                             | $BV_{DSS}$    | 30        | —   | —                   | V             | $V_{GS} = 0V, I_D = 250\mu\text{A}$   |
| Zero Gate Voltage Drain Current @ $T_C = 25^\circ\text{C}$ | $I_{DSS}$     | —         | —   | 1                   | $\mu\text{A}$ | $V_{DS} = 30V, V_{GS} = 0V$   |
| Gate-Body Leakage  | $I_{GSS}$     | —         | —   | $\pm 10$<br>$\pm 1$ | $\mu\text{A}$ | $V_{GS} = \pm 10V, V_{DS} = 0V$<br>$V_{GS} = \pm 5V, V_{DS} = 0V$   |
| <b>ON CHARACTERISTICS (Note 4)</b>                         |               |           |     |                     |               |   |
| Gate Threshold Voltage                                     | $V_{GS(th)}$  | 0.6       | —   | 1.2                 | V             | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$   |
| Static Drain-Source On-Resistance                          | $R_{DS(on)}$  | —         | —   | 2.2<br>1.5<br>1.2   | $\Omega$      | $V_{GS} = 1.8V, I_D = 20\text{mA}$<br>$V_{GS} = 2.5V, I_D = 20\text{mA}$<br>$V_{GS} = 4.0V, I_D = 100\text{mA}$ |
| Forward Transconductance                                   | $ Y_{fs} $    | 100       | —   | —                   | mS            | $V_{DS} = 10V, I_D = 0.1A$  |
| Source-Drain Diode Forward Voltage                         | $V_{SD}$      | 0.5       | —   | 1.4                 | V             | $V_{GS} = 0V, I_S = 115\text{mA}$   |
| <b>DYNAMIC CHARACTERISTICS</b>                             |               |           |     |                     |               |   |
| Input Capacitance  | $C_{iss}$     | —         | 39  | —                   | pF            | $V_{DS} = 3V, V_{GS} = 0V$<br>$f = 1.0\text{MHz}$   |
| Output Capacitance   | $C_{oss}$     | —         | 10  | —                   | pF            |   |
| Reverse Transfer Capacitance                               | $C_{rss}$     | —         | 3.6 | —                   | pF            |   |
| Switching Time   | Turn-on Time  | $t_{on}$  | —   | 11                  | nS            | $V_{DD} = 5V, I_D = 10\text{mA},$<br>$V_{GS} = 0-5V$  |
|  | Turn-off Time | $t_{off}$ | —   | 51                  | nS            |   |

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Short duration pulse test used to minimize self-heating effect.

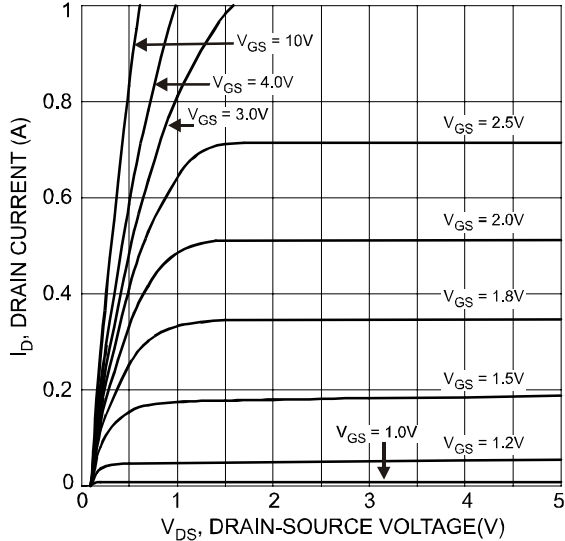


Fig. 1 Typical Output Characteristics

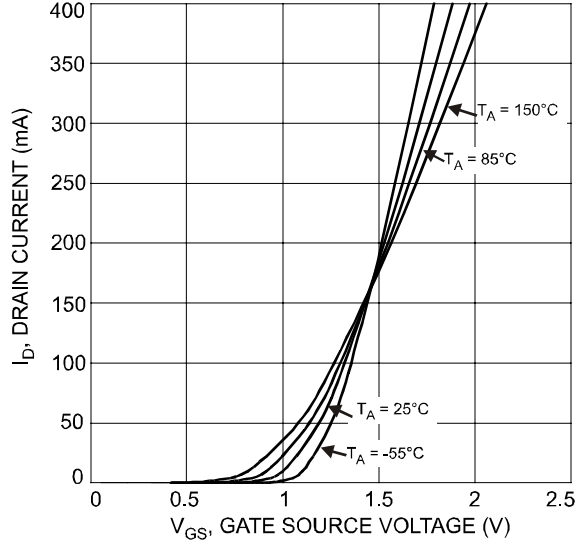


Fig. 2 Typical Transfer Characteristics

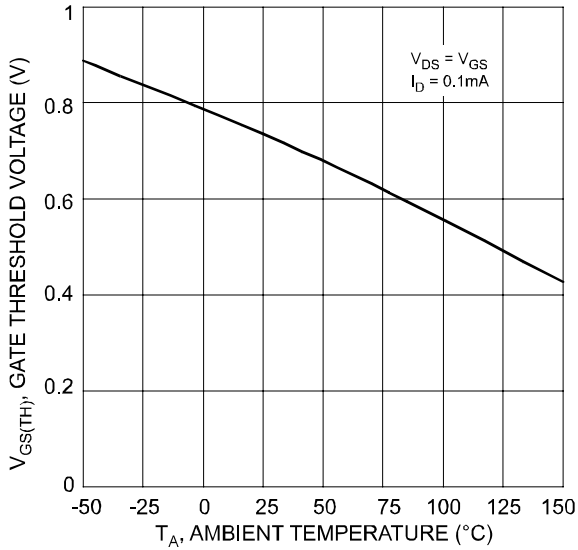


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

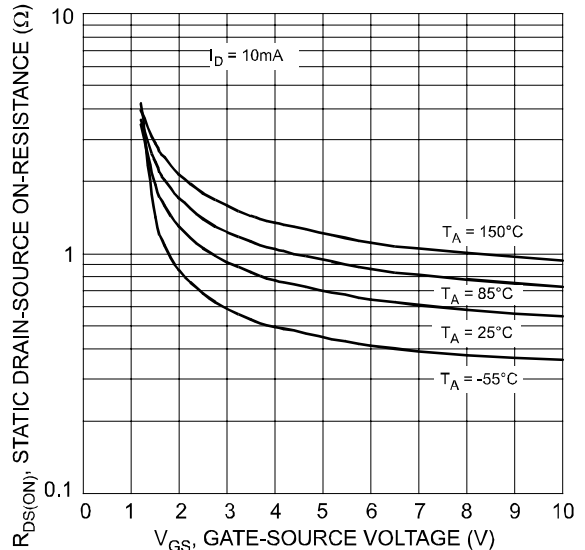


Fig. 4 Static Drain-Source On-Resistance vs. Gate-Source Voltage

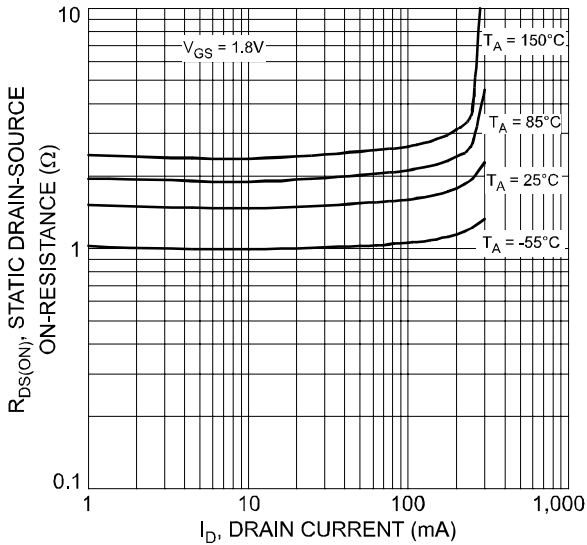


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

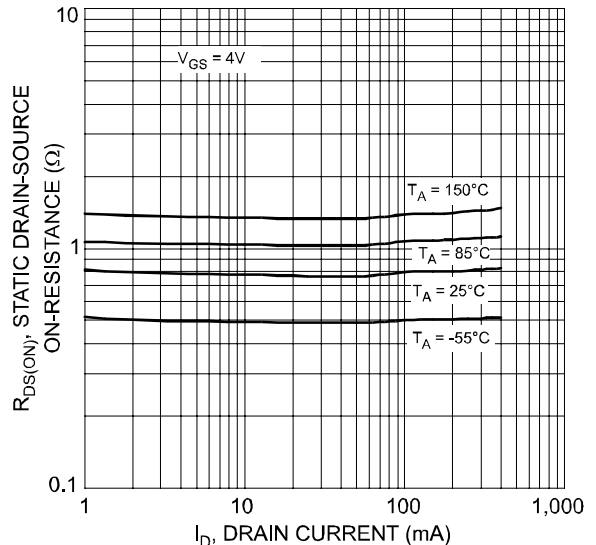


Fig. 6 Static Drain-Source On-Resistance vs. Drain Current

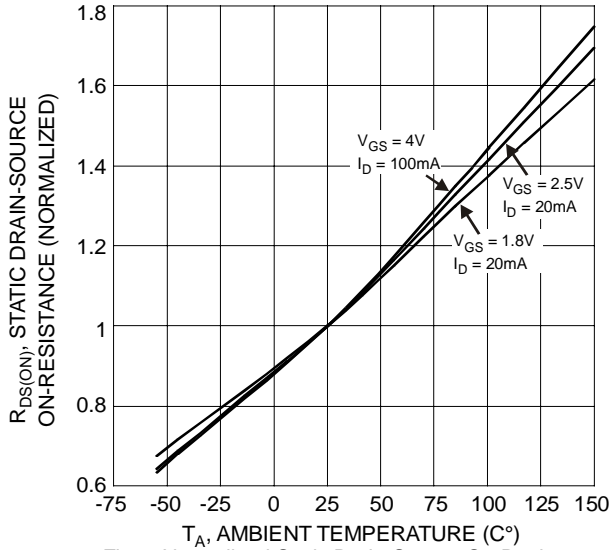


Fig. 7 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

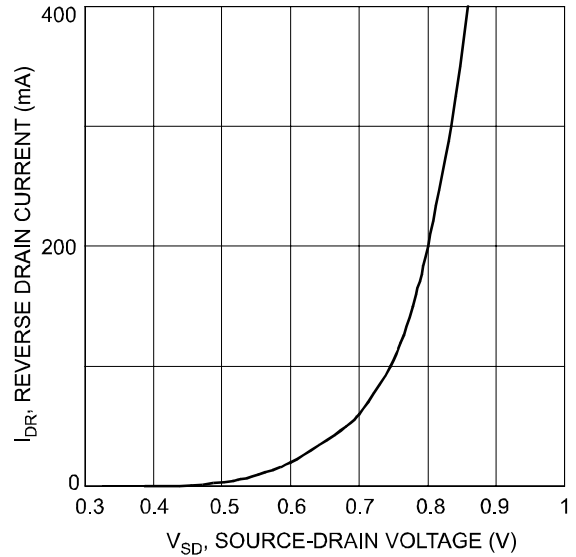


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

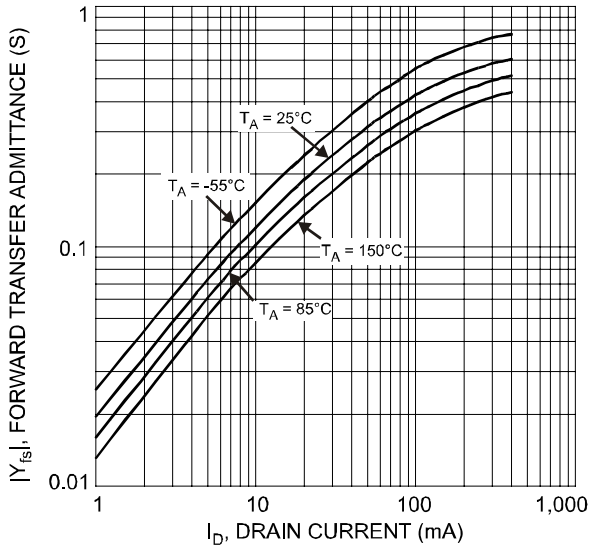


Fig. 9 Forward Transfer Admittance vs. Drain Current

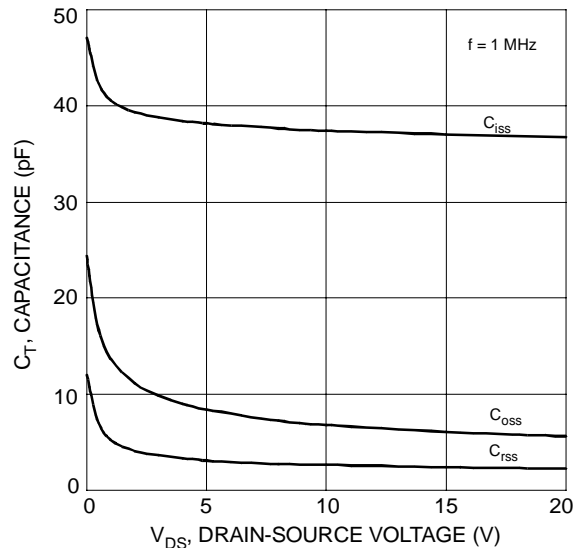


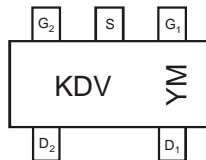
Fig. 10 Typical Capacitance

**Ordering Information** (Note 5)

| Part Number  | Case    | Packaging        |
|--------------|---------|------------------|
| DMN32D2LDF-7 | SOT-353 | 3000/Tape & Reel |

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information** (Note 6)



KDV = Product Type Marking Code (See Note 6)  
 YM = Date Code Marking  
 Y = Year ex: U = 2007  
 M = Month ex: 9 = September

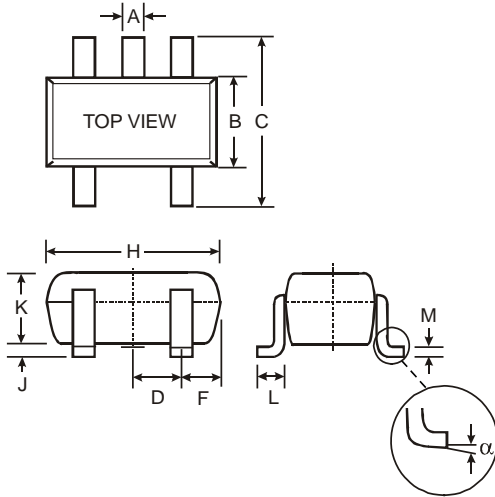
Notes: 6. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

**Date Code Key**

| Year | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 |
|------|------|------|------|------|------|------|
| Code | U    | V    | W    | X    | Y    | Z    |

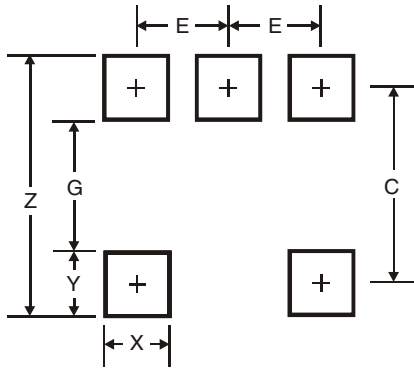
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Package Outline Dimensions**



| SOT-353              |              |      |
|----------------------|--------------|------|
| Dim                  | Min          | Max  |
| A                    | 0.10         | 0.30 |
| B                    | 1.15         | 1.35 |
| C                    | 2.00         | 2.20 |
| D                    | 0.65 Nominal |      |
| F                    | 0.30         | 0.40 |
| H                    | 1.80         | 2.20 |
| J                    | —            | 0.10 |
| K                    | 0.90         | 1.00 |
| L                    | 0.25         | 0.40 |
| M                    | 0.10         | 0.25 |
| α                    | 0°           | 8°   |
| All Dimensions in mm |              |      |

**Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.5           |
| G          | 1.3           |
| X          | 0.42          |
| Y          | 0.6           |
| C          | 1.9           |
| E          | 0.65          |

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